# 74LVC2G241

# Dual buffer/line driver; 3-state

Rev. 13 — 8 April 2013

**Product data sheet** 

### 1. General description

The 74LVC2G241 is a dual non-inverting buffer/line driver with 3-state outputs. The 3-state outputs are controlled by the output enable inputs 1OE and 2OE:

- A HIGH level at pin 10E causes output 1Y to assume a high-impedance OFF-state.
- A LOW level at pin 2OE causes output 2Y to assume a high-impedance OFF-state.

Schmitt trigger action at all inputs makes the circuit highly tolerant of slower input rise and fall times.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of the 74LVC2G241 as a translator in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

#### 2. Features and benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant input/output for interfacing with 5 V logic
- High noise immunity
- Complies with JEDEC standard:
  - ◆ JESD8-7 (1.65 V to 1.95 V)
  - ◆ JESD8-5 (2.3 V to 2.7 V)
  - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
  - ♦ HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- $\pm$  24 mA output drive (V<sub>CC</sub> = 3.0 V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



# 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC2G241DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC2G241DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74LVC2G241GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 $\times$ 1.95 $\times$ 0.5 mm	SOT833-1
74LVC2G241GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 $\times$ 1 $\times$ 0.5 mm	SOT1089
74LVC2G241GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 3 $\times$ 2 $\times$ 0.5 mm	SOT996-2
74LVC2G241GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 $\times$ 1.6 $\times$ 0.5 mm	SOT902-2
74LVC2G241GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 $\times$ 1.0 $\times$ 0.35 mm	SOT1116
74LVC2G241GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203

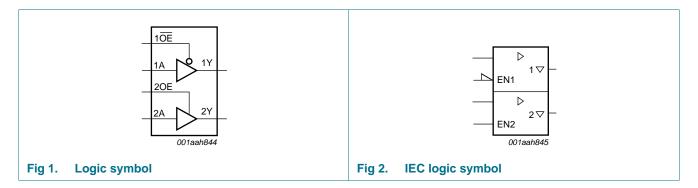
# 4. Marking

Table 2. Marking codes

Type number	Marking code <sup>[1]</sup>
74LVC2G241DP	V241
74LVC2G241DC	V41
74LVC2G241GT	V41
74LVC2G241GF	V1
74LVC2G241GD	V41
74LVC2G241GM	V41
74LVC2G241GN	V1
74LVC2G241GS	V1

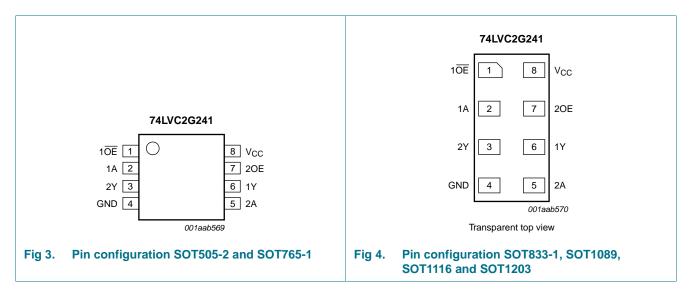
<sup>[1]</sup> The pin 1 indicator is located on the lower left corner of the device, below the marking code.

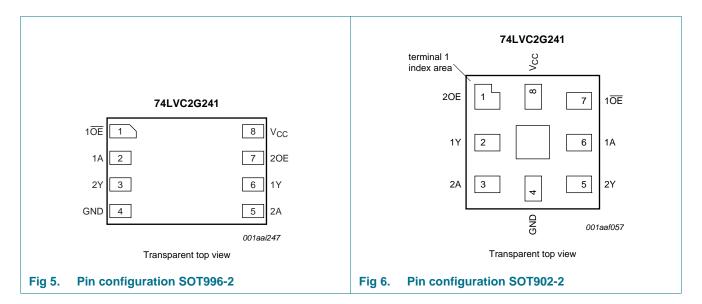
## 5. Functional diagram



## 6. Pinning information

### 6.1 Pinning





### 6.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT505-2, SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2	
1 <del>OE</del>	1	7	output enable input (active LOW)
1A, 2A	2, 5	6, 3	data input
GND	4	4	ground (0 V)
1Y, 2Y	6, 3	2, 5	data output
20E	7	1	output enable input (active HIGH)
V <sub>CC</sub>	8	8	supply voltage

# 7. Functional description

Table 4. Function table[1]

Input				Output		
1OE	1A	20E	2A	1Y	2Y	
L	L	Н	L	L	L	
L	Н	Н	Н	Н	Н	
Н	X	L	X	Z	Z	

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+6.5	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-50	-	mA
VI	input voltage		[ <u>1]</u> -0.5	+6.5	V
I <sub>OK</sub>	output clamping current	$V_O > V_{CC}$ or $V_O < 0 \text{ V}$	-	±50	mA
Vo	output voltage	enable mode	[ <u>1]</u> -0.5	$V_{CC} + 0.5$	V
		disable mode	[ <u>1]</u> -0.5	+6.5	V
		Power-down mode	[1][2] -0.5	+6.5	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±50	mA
I <sub>CC</sub>	supply current		-	100	mA
I <sub>GND</sub>	ground current		-100	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	[3] _	300	mW

<sup>[1]</sup> The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

## 9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		1.65	5.5	V
$V_{I}$	input voltage		0	5.5	V
Vo	output voltage	$V_{CC}$ = 1.65 V to 5.5 V; enable mode	0	$V_{CC}$	V
		V <sub>CC</sub> = 1.65 V to 5.5 V; disable mode	0	5.5	V
		V <sub>CC</sub> = 0 V; Power-down mode	0	5.5	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V <sub>CC</sub> = 1.65 V to 2.7 V	-	20	ns/V
		V <sub>CC</sub> = 2.7 V to 5.5 V	-	10	ns/V

<sup>[2]</sup> When  $V_{CC} = 0 \text{ V}$  (Power-down mode), the output voltage can be 5.5 V in normal operation.

<sup>[3]</sup> For TSSOP8 packages: above 55 °C the value of P<sub>tot</sub> derates linearly at 2.5 mW/K.
For VSSOP8 packages: above 110 °C the value of P<sub>tot</sub> derates linearly at 8.0 mW/K.
For XSON8 and XQFN8 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

## 10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
T <sub>amb</sub> = -	40 °C to +85 °C					
$V_{IH}$	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
$V_{IL}$	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O}$ = 100 $\mu$ A; $V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.45	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.3	V
		$I_{O}$ = 12 mA; $V_{CC}$ = 2.7 V	-	-	0.4	V
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_O = -100 \ \mu A; \ V_{CC} = 1.65 \ V \ to \ 5.5 \ V$	$V_{CC}-0.1$	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	V
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.3	-	-	V
		$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.8	-	-	V
I <sub>I</sub>	input leakage current	$V_I = 5.5 \text{ V or GND}$ ; $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	±0.1	±5	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = 5.5$ V or GND; $V_{CC} = 3.6$ V	-	±0.1	±10	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O} = 5.5 \text{ V}$ ; $V_{CC} = 0 \text{ V}$	-	±0.1	±10	μΑ
I <sub>CC</sub>	supply current	$V_I = 5.5 \text{ V or GND}; I_O = 0 \text{ A};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	-	0.1	10	μΑ
$\Delta I_{CC}$	additional supply current	per pin; $V_I = V_{CC} - 0.6 \text{ V}$ ; $I_O = 0 \text{ A}$ ; $V_{CC} = 2.3 \text{ V}$ to 5.5 V	-	5	500	μΑ
C <sub>I</sub>	input capacitance		-	2	-	pF

 Table 7.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
T <sub>amb</sub> = -	-40 °C to +125 °C					
$V_{IH}$	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
$V_{IL}$	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	$0.3 \times V_{CC}$	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O}$ = 100 $\mu$ A; $V_{CC}$ = 1.65 V to 5.5 V	-	-	0.1	V
		$I_{O} = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.70	V
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_{O}$ = 12 mA; $V_{CC}$ = 2.7 V	-	-	0.60	V
		$I_{O} = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.80	V
		$I_{O} = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.80	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$				
		$I_{O} = -100 \ \mu A; \ V_{CC} = 1.65 \ V \ to \ 5.5 \ V$	$V_{CC}-0.1$	-	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	0.95	-	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.7	-	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	1.9	-	-	V
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	-	-	V
		$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.4	-	-	V
I <sub>I</sub>	input leakage current	$V_I = 5.5 \text{ V or GND}$ ; $V_{CC} = 0 \text{ V to } 5.5 \text{ V}$	-	-	±20	μΑ
l <sub>OZ</sub>	OFF-state output current	$V_I = V_{IH}$ or $V_{IL}$ ; $V_O = 5.5$ V or GND; $V_{CC} = 3.6$ V	-	-	±20	μΑ
I <sub>OFF</sub>	power-off leakage current	$V_{I}$ or $V_{O} = 5.5 \text{ V}$ ; $V_{CC} = 0 \text{ V}$	-	-	±20	μΑ
I <sub>CC</sub>	supply current	$V_I = 5.5 \text{ V or GND}; I_O = 0 \text{ A};$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	-	-	40	μΑ
$\Delta I_{CC}$	additional supply current	per pin; $V_I = V_{CC} - 0.6 \text{ V}$ ; $I_O = 0 \text{ A}$ ; $V_{CC} = 2.3 \text{ V}$ to 5.5 V	-	-	5	mA

<sup>[1]</sup> Typical values are measured at  $V_{CC}$  = 3.3 V and  $T_{amb}$  = 25 °C.

## 11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10.

Symbol	Parameter	Conditions		-40	0 °C to +85 °	°C	-40 °C t	o +125 °C	Unit
				Min	Typ[1]	Max	Min	Max	
t <sub>pd</sub>	propagation delay	nA to nY; see Figure 7	[2]		'		'	'	
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.0	4.5	8.8	1.0	11.0	ns
	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.5	2.8	4.9	0.5	6.3	ns	
		$V_{CC} = 2.7 \text{ V}$		1.0	2.8	4.7	1.0	5.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.5	2.6	4.3	0.5	5.4	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.5	2.1	3.7	0.5	4.6	ns
t <sub>en</sub>	enable time	1OE to 1Y; see Figure 8	[3]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.5	5.2	9.9	1.5	12.4	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.0	3.1	5.6	1.0	7.0	ns
		$V_{CC} = 2.7 \text{ V}$		1.5	3.2	5.5	1.5	6.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		0.5	2.7	4.7	0.5	5.9	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.5	2.0	3.8	0.5	4.8	ns
		2OE to 2Y; see Figure 9	[3]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.0	4.3	8.8	1.0	11.0	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		1.0	2.7	4.7	1.0	5.9	ns
		$V_{CC} = 2.7 \text{ V}$		1.0	2.7	4.6	1.0	5.8	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.0	2.5	4.1	1.0	5.1	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.5	1.9	3.3	0.5	4.1	ns
t <sub>dis</sub>	disable time	1OE to 1Y; see Figure 8	[4]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.0	3.2	11.6	1.0	14.1	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.5	2.2	5.8	0.5	7.6	ns
		$V_{CC} = 2.7 \text{ V}$		1.0	2.8	4.6	1.0	5.9	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.0	2.6	4.4	1.0	5.7	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.5	2.0	3.4	0.5	4.6	ns
		2OE to 2Y; see Figure 9	[4]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$		1.0	3.6	12.5	1.0	15.2	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.5	2.0	5.2	0.5	6.9	ns
		$V_{CC} = 2.7 \text{ V}$		1.5	3.2	4.9	1.5	6.3	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$		1.0	2.8	4.2	1.0	5.4	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.5	2.0	3.3	0.5	4.4	ns

 Table 8.
 Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 10.

Symbol	Parameter	Conditions	nditions –40 °C to +85 °C		–40 °C to	Unit			
				Min	Typ[1]	Max	Min	Max	
$C_{PD}$	power dissipation	per buffer; $V_I = GND$ to $V_{CC}$	[5]						
	capacitance	output enabled		-	20	-	-	-	pF
		output disabled		-	5	-	-	-	pF

- [1] Typical values are measured at nominal  $V_{CC}$  and at  $T_{amb}$  = 25 °C.
- [2]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [3]  $t_{en}$  is the same as  $t_{PZH}$  and  $t_{PZL}$ .
- [4]  $t_{dis}$  is the same as  $t_{PLZ}$  and  $t_{PHZ}$ .
- [5]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu W$ ).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$  where:

f<sub>i</sub> = input frequency in MHz;

fo = output frequency in MHz;

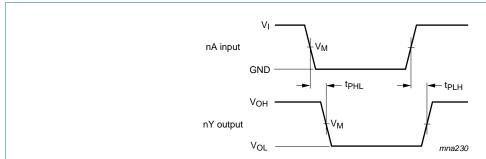
C<sub>L</sub> = output load capacitance in pF;

V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$  = sum of outputs.

### 12. Waveforms



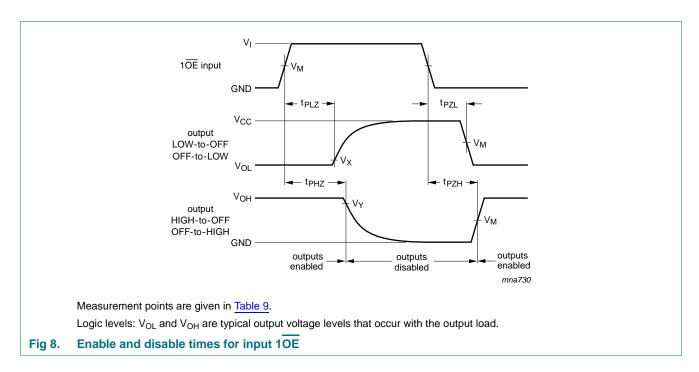
Measurement points are given in Table 9.

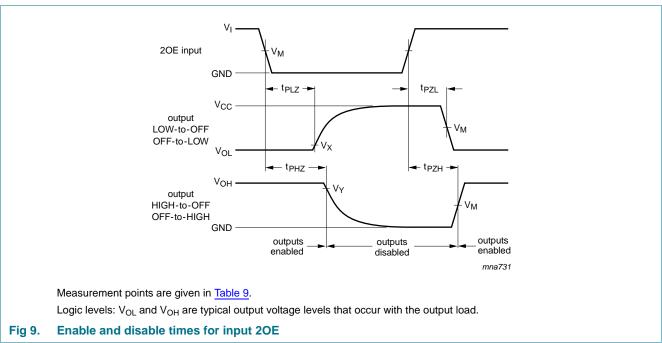
Logic levels: V<sub>OL</sub> and V<sub>OH</sub> are typical output voltage levels that occur with the output load.

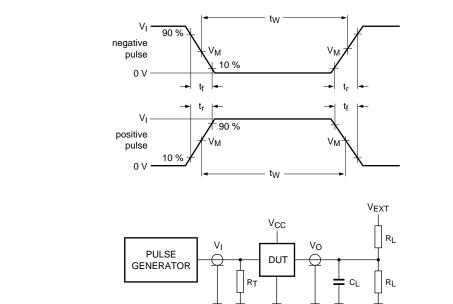
Fig 7. The data input (nA) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Input	Output		
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>
1.65 V to 1.95 V	$0.5 \times V_{\text{CC}}$	$0.5 \times V_{CC}$	V <sub>OL</sub> + 0.15 V	$V_{OH} - 0.15 V$
2.3 V to 2.7 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL} + 0.15 V$	$V_{OH}-0.15\ V$
2.7 V	1.5 V	1.5 V	$V_{OL}$ + 0.3 $V$	$V_{OH}-0.3\ V$
3.0 V to 3.6 V	1.5 V	1.5 V	$V_{OL}$ + 0.3 $V$	$V_{OH}-0.3\ V$
4.5 V to 5.5 V	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$V_{OL}$ + 0.3 V	$V_{OH} - 0.3 V$







Test data is given in Table 10.

Definitions for test circuit:

 $R_L$  = Load resistance.

 $C_L$  = Load capacitance including jig and probe capacitance.

 $R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

V<sub>EXT</sub> = Test voltage for switching times.

Fig 10. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Input	Load	Load		V <sub>EXT</sub>		
	VI	CL	R <sub>L</sub>	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub>	
1.65 V to 1.95 V	$V_{CC}$	30 pF	1 kΩ	open	GND	$2\times V_{CC}$	
2.3 V to 2.7 V	$V_{CC}$	30 pF	500 Ω	open	GND	$2\times V_{CC}$	
2.7 V	2.7 V	50 pF	500 Ω	open	GND	6 V	
3.0 V to 3.6 V	2.7 V	50 pF	$500 \Omega$	open	GND	6 V	
4.5 V to 5.5 V	$V_{CC}$	50 pF	$500 \Omega$	open	GND	$2\times V_{CC}$	

001aae235

## 13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

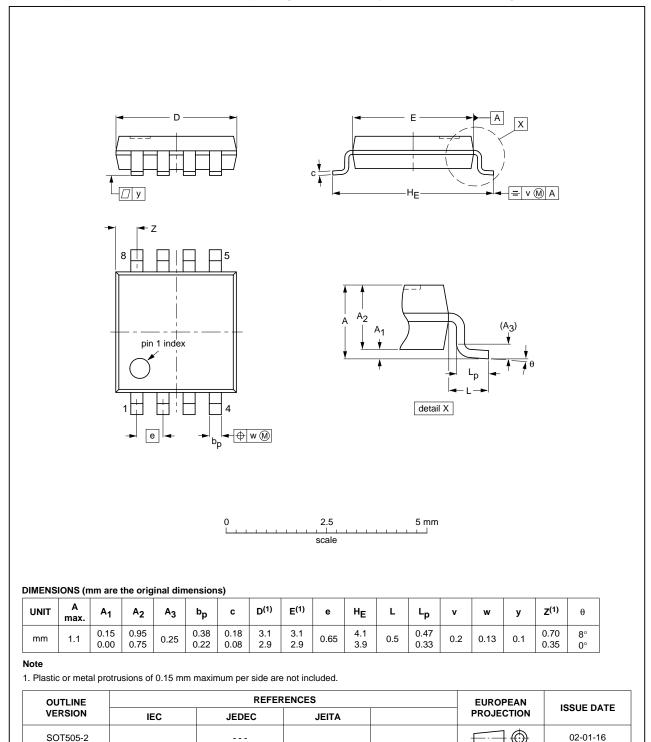
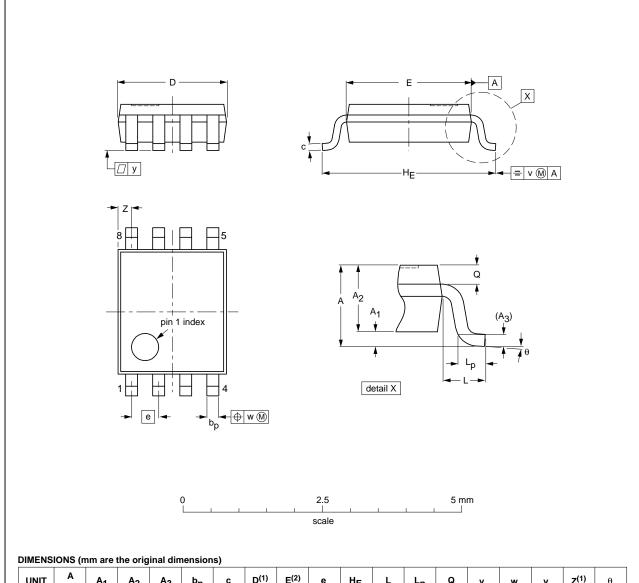


Fig 11. Package outline SOT505-2 (TSSOP8)

VC2G241 All information provided in this document is subject to legal disclaimers.

#### VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	А3	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	Q	٧	w	у	Z <sup>(1)</sup>	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

#### Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT765-1		MO-187				02-06-07	

Fig 12. Package outline SOT765-1 (VSSOP8)

74LVC2G241

All information provided in this document is subject to legal disclaimers.

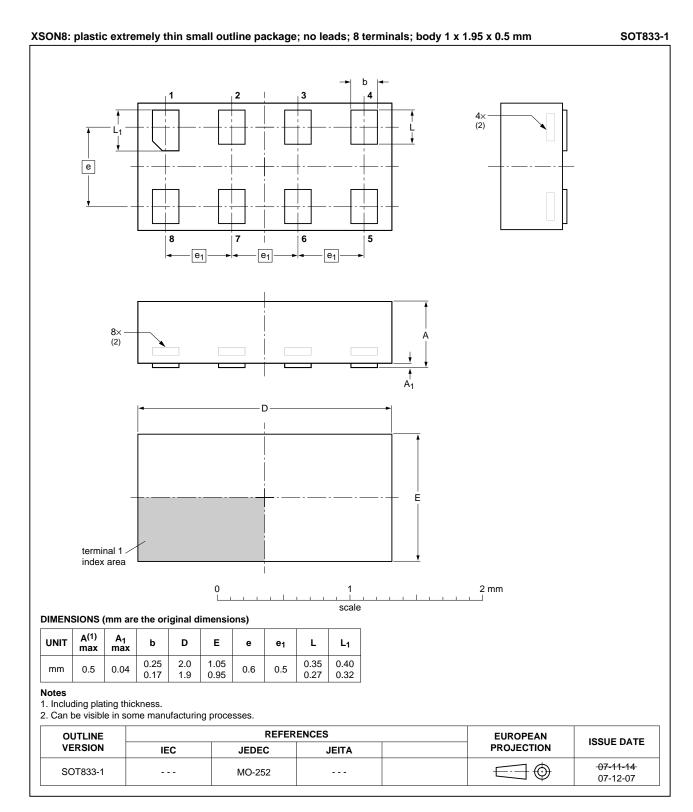


Fig 13. Package outline SOT833-1 (XSON8)

© NXP B.V. 2013. All rights reserved.

14 of 23

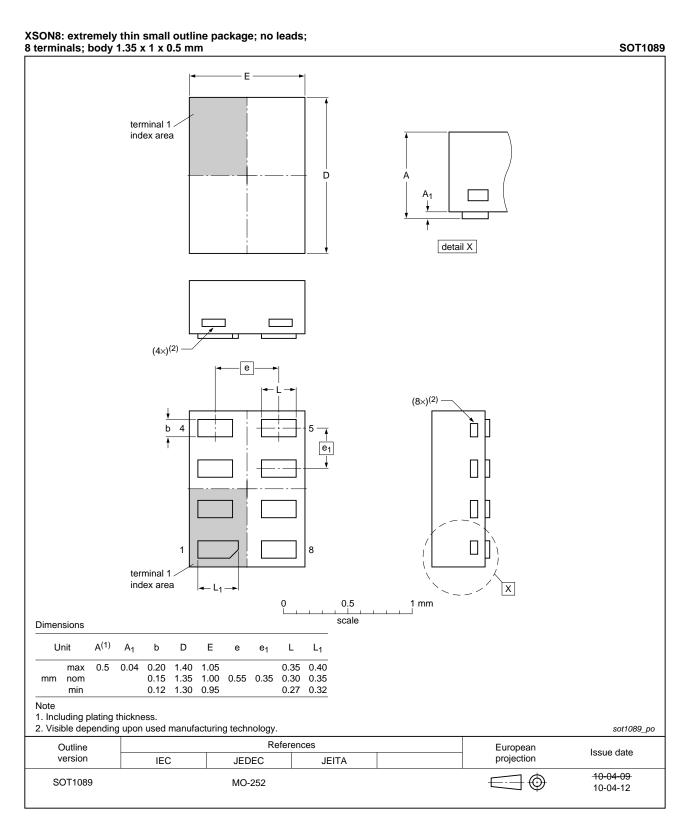


Fig 14. Package outline SOT1089 (XSON8)

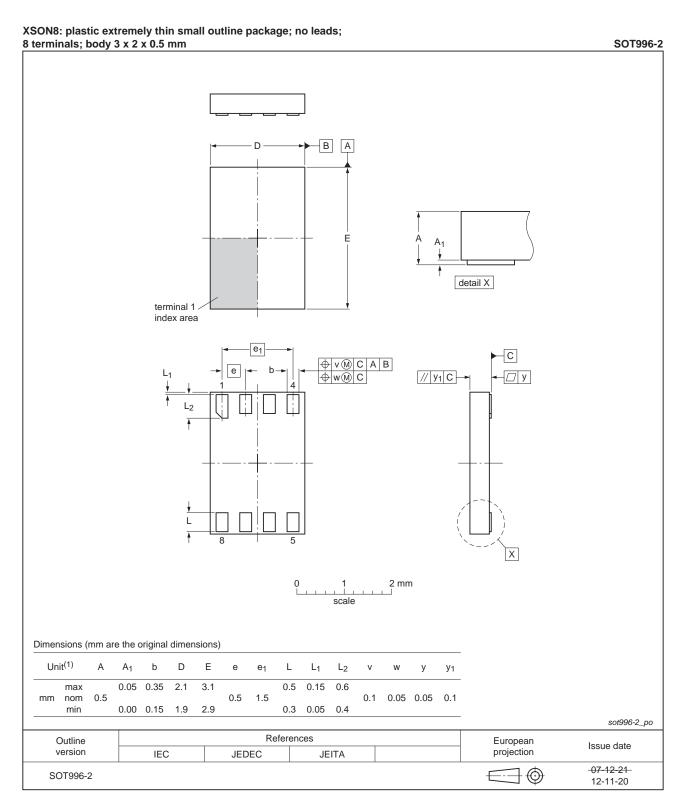


Fig 15. Package outline SOT996-2 (XSON8)

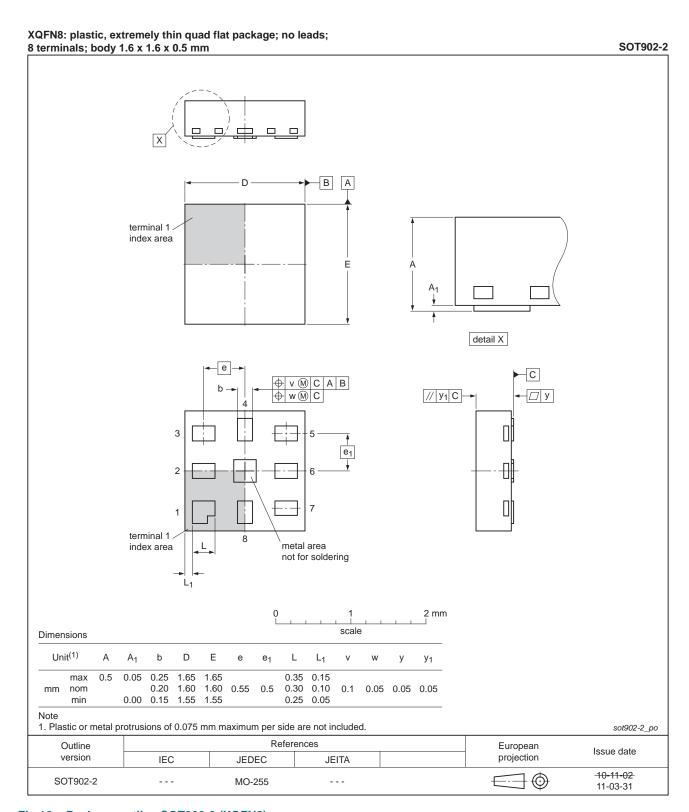


Fig 16. Package outline SOT902-2 (XQFN8)

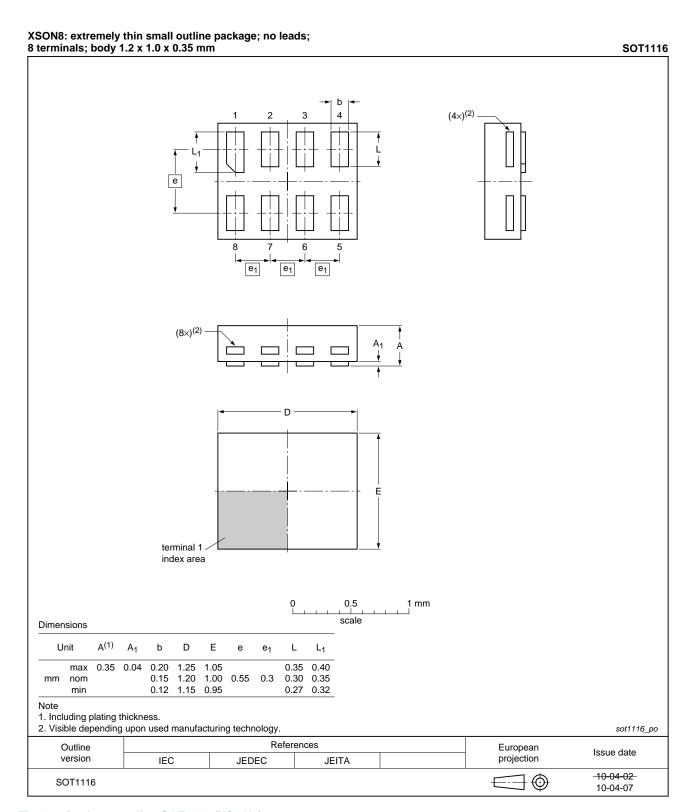


Fig 17. Package outline SOT1116 (XSON8)

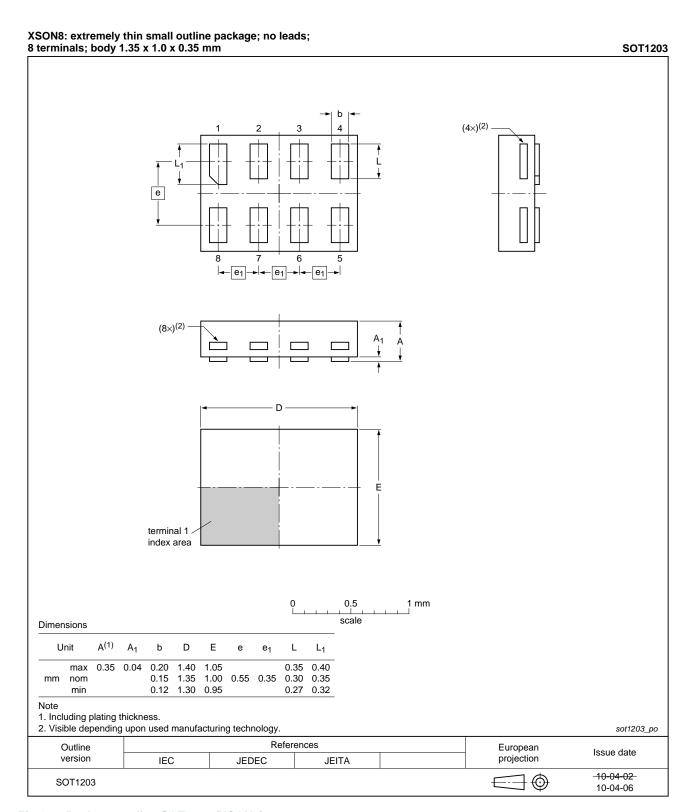


Fig 18. Package outline SOT1203 (XSON8)

74LVC2G241

All information provided in this document is subject to legal disclaimers.

## 14. Abbreviations

#### Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 15. Revision history

#### Table 12. Revision history

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G241 v.13	20130408	Product data sheet	-	74LVC2G241 v.12
Modifications:	<ul> <li>For type nu</li> </ul>	mber 74LVC2G241GD XSC	N8U has changed to X	SON8.
74LVC2G241 v.12	20120622	Product data sheet	-	74LVC2G241 v.11
Modifications:	<ul> <li>For type nu</li> </ul>	mber 74LVC2G241GM the	SOT code has changed	I to SOT902-2.
74LVC2G241 v.11	20111129	Product data sheet	-	74LVC2G241 v.10
Modifications:	<ul> <li>Legal pages</li> </ul>	s updated.		
74LVC2G241 v.10	20100806	Product data sheet	-	74LVC2G241 v.9
74LVC2G241 v.9	20080610	Product data sheet	-	74LVC2G241 v.8
74LVC2G241 v.8	20080312	Product data sheet	-	74LVC2G241 v.7
74LVC2G241 v.7	20071005	Product data sheet	-	74LVC2G241 v.6
74LVC2G241 v.6	20060922	Product data sheet	-	74LVC2G241 v.5
74LVC2G241 v.5	20050202	Product specification	-	74LVC2G241 v.4
74LVC2G241 v.4	20040922	Product specification	-	74LVC2G241 v.3
74LVC2G241 v.3	20030311	Product specification	-	74LVC2G241 v.2
74LVC2G241 v.2	20030129	Product specification	-	74LVC2G241 v.1
74LVC2G241 v.1	20021030	Product specification	-	-

### 16. Legal information

#### 16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

#### 16.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

**Product specification** — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

#### 16.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information. NXP Semiconductors takes no responsibility for the content in this document if provided by an information source outside of NXP Semiconductors.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in life support, life-critical or safety-critical systems or equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors and its suppliers accept no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nxp.com/profile/terms">http://www.nxp.com/profile/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

74LVC2G241

All information provided in this document is subject to legal disclaimers.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from competent authorities.

Non-automotive qualified products — Unless this data sheet expressly states that this specific NXP Semiconductors product is automotive qualified, the product is not suitable for automotive use. It is neither qualified nor tested in accordance with automotive testing or application requirements. NXP Semiconductors accepts no liability for inclusion and/or use of non-automotive qualified products in automotive equipment or applications.

In the event that customer uses the product for design-in and use in automotive applications to automotive specifications and standards, customer (a) shall use the product without NXP Semiconductors' warranty of the

product for such automotive applications, use and specifications, and (b) whenever customer uses the product for automotive applications beyond NXP Semiconductors' specifications such use shall be solely at customer's own risk, and (c) customer fully indemnifies NXP Semiconductors for any liability, damages or failed product claims resulting from customer design and use of the product for automotive applications beyond NXP Semiconductors' standard warranty and NXP Semiconductors' product specifications.

#### 16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

#### 17. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: <a href="mailto:salesaddresses@nxp.com">salesaddresses@nxp.com</a>

74LVC2G241

#### Dual buffer/line driver; 3-state

## 18. Contents

1	General description
2	Features and benefits
3	Ordering information 2
4	Marking 2
5	Functional diagram 3
6	Pinning information 3
6.1	Pinning
6.2	Pin description 4
7	Functional description 4
8	Limiting values 5
9	Recommended operating conditions 5
10	Static characteristics 6
11	Dynamic characteristics 8
12	Waveforms
13	Package outline
14	Abbreviations
15	Revision history
16	Legal information
16.1	Data sheet status 21
16.2	Definitions
16.3	Disclaimers
16.4	Trademarks
17	Contact information 22
18	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.